NSN 5962-01-371-3181

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Maximum Power Dissipation Rating:

2.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Enditem e/i fscm 03950

Features Provided:

Bipolar and monolithic and programmed

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Bipolar metal-oxide semiconductor

Input Circuit Pattern:

16 input

Case Outline Source And Designator:

D-8 mil-m-38510

Current Rating Per Characteristic:

100.00 milliamperes reverse current, dc

Product Name:

Microcircuit bipolar pal, 16-input 8-output and-or invert gate array

Voltage Rating And Type Per Characteristic:

-1.5 volts absolute input and 12.0 volts absolute input

Memory Device Type:

Pal

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Specification Data:

81349--38510/50401brx government specification

Purchase Description Identification:

05869-53217-1

Departure From Cited Designator:

Altered by programming, testing & marking

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0

